

**B.Tech. – VIEP – ELECTRICAL ENGINEERING  
(BTELVI)**

**Term-End Examination**

**December, 2015**

00418

**BIEE-013 : ELECTRICAL AND ELECTRONICS  
ENGINEERING MATERIALS**

*Time : 3 hours*

*Maximum Marks : 70*

**Note :**

- (i) *Attempt any seven questions.*
- (ii) *All questions carry equal marks.*
- (iii) *Symbols used have their usual meanings.*
- (iv) *Use of scientific calculator is allowed.*

1. (a) What are Miller indices ? Name at least six features of Miller indices. 5

(b) Find the Miller indices of a plane that makes intercepts 1 on x-axis, 2 on y-axis and is parallel to z-axis. Also sketch the plane in a simple cubic cell. 5

2. (a) Explain Bragg's law of X-ray diffraction. Show that the condition for reflection is given by  $2d \sin \theta = n\lambda$ . 5
- (b) The Bragg's angle for first order deflection from (111) plane in a crystal is  $30^\circ$ , when the wavelength of X-ray is  $1.75 \text{ \AA}$ . Calculate the lattice parameter 'a'. Given  $(hkl) = (111)$ . 5
3. Give a brief account of the band theory of solids. Explain the classification of solids into conductors, semiconductors and insulators on the basis of band theory. 10
4. (a) Define the terms : mean free path ( $\lambda$ ), mobility ( $\mu$ ) and collision time ( $\tau$ ). 5
- (b) On the basis of electron theory, show that the expression of conductivity is given by
- $$\sigma = \frac{ne^2\tau}{m} \quad 5$$
5. (a) Explain the Hall effect in semiconductor material. 5
- (b) Discuss the Type I and Type II superconductors with relevant diagrams. 5
6. (a) As the concentration of electrons in a semi-conductor is changed by changing the impurity level, the conductivity also changes. Show that it passes through a minimum, when  $n_e = n_i \sqrt{\frac{\mu_h}{\mu_e}}$  and find the minimum value.  $n_i$  is the intrinsic concentration. 5

- (b) The resistivity of pure germanium at room temperature is  $0.47 \Omega\text{-m}$ . Find the carrier density of Germanium at the room temperature for the electron mobility ( $\mu_e$ ) of  $0.42\text{m}^2/\text{volt-sec}$  and hole mobility ( $\mu_h$ ) of  $0.20\text{m}^2/\text{volt-sec}$ . 5
7. What are drift current and diffusion current? Find the expression for each of them. Also derive the expression of the continuity equation. 10
8. (a) Explain the origins of permanent magnet dipoles in matters. 5
- (b) The saturation induction of Nickel is  $0.65$  Tesla. If the density of Nickel is  $8906 \text{ kg/m}^3$  and the atomic weight is  $58.7$ , calculate the magnetic moment of Nickel atom. Avogadro number is  $6.23 \times 10^{26}/\text{mole}$ . 5
9. (a) Distinguish between ferromagnetism and antiferromagnetism. 5
- (b) Explain domain theory for ferromagnetic materials. 5
10. Write short notes on any *two* of the following :  $2 \times 5 = 10$
- (a) Crystal growth
- (b) Low resistivity materials versus High resistivity materials
- (c) IGFET
- (d) Permanent magnet materials